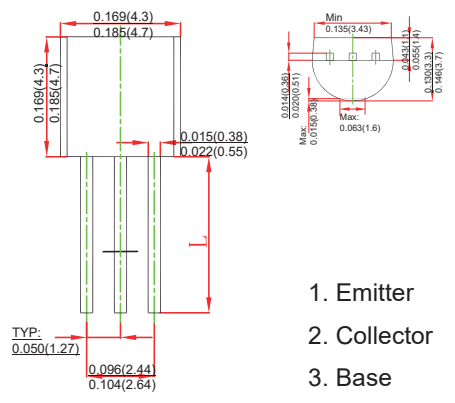
TO-92 Plastic-Encapsulate Transistors

FEATURES

- Low Frequency Amplifier
- TRANSISTOR (NPN)

MECHANICAL DATA

- Case style:TO-92 molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	35	V
Collector-Emitter Voltage	V_{CEO}	35	V
Emitter-Base Voltage	V_{EBO}	4	V
Collector Current -Continuous	I_C	0.5	A
Collector Power Dissipation	P_C	400	mW
Thermal Resistance from Junction to Ambient	RθJA	312	℃ /W
Junction Temperature	T_j	150	℃
Storage Temperature	T_{stg}	- 50 ~ +150	℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C= 0.01mA,I_E=0	35			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=1mA,I_B=0	35			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=0.01mA,I_C=0	4			V
Collector cut-off current	I_{CBO}	V_{CB}=20V,I_E=0			0.5	uA
Emitter cut-off current	I_{EBO}	V_{EB}=3V,I_C=0			0.1	uA
DC current gain	$h_{FE(1)}$	V_{CE}=3V, I_C=10mA	60		320	
	$h_{FE(2)}$	V_{CE}=3V, I_C=500mA	10			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=150mA,I_B=15mA			0.6	V
Base-emitter voltage	V_{BE}	V_{CE}=3V, I_C=10mA			0.75	V